## What Can We Do with Low Energy Electron Microscopy?

A technique Using low energy elastically back-scattered electrons

Imaging

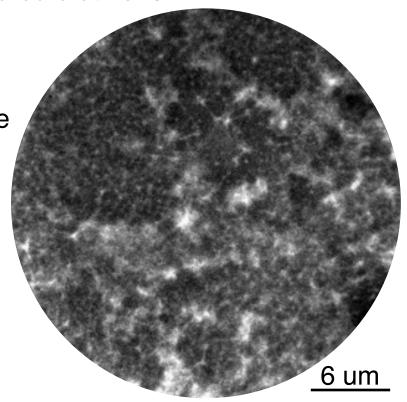
Microscopy

 Diffraction on conductive surface

Energy 0 – 100 eV

Wavelength λ ≥1 Å

Surface sensitive



Surface Dynamics of Si(111)@900°C

**Temperature** 

Electron energy

Gas Dosing

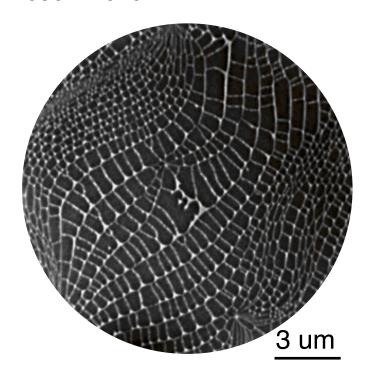
Material Deposition

Time

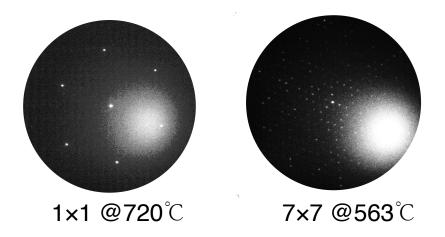
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## Phase Transition Between 7×7 and 1×1 on Si(111) Surface

Transition temperature range 650°C ~670°C

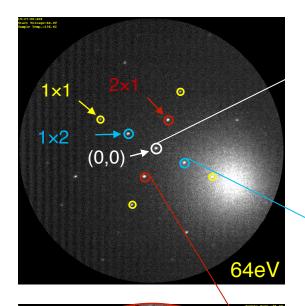


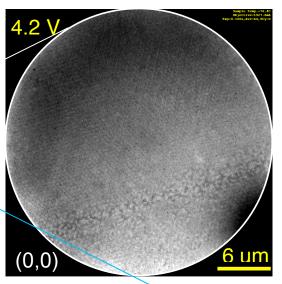
**Phase Transition** 

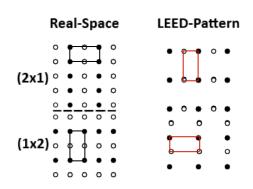


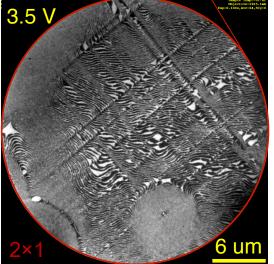
- Dark area 7×7, bright area 1×1
- 7×7 domain start from the step edge and grow along the up step direction

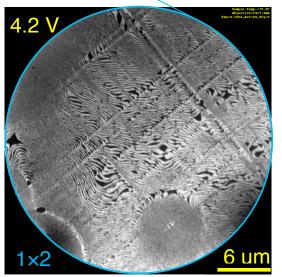
## Bright and Dark Field Images on Si(100)





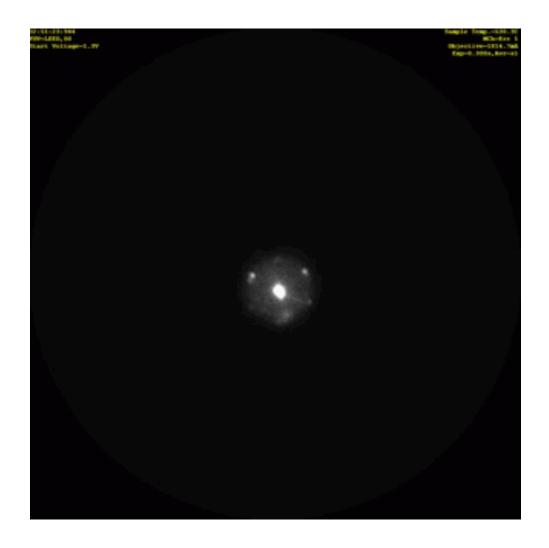






In Dark field image, only domains that contribute to the selected LEED spot become bright.

Very sensitive to materials with different domains or rotation angles.



Energy Ramp of Low energy electron diffraction (LEED)